

Amendments to the claims:

Please withdraw claims 2 and 3. Cancel claims 4, 8-9, 11, and 18. Add new claim 20. Amend claims 1, 12-17, and 19, as follows:

Claim 1 (currently amended): A chip for a chip-containing portable article, [in particular an article of card format] the chip comprising a silicon substrate layer [whose] having an active face [has] with circuits integrated therein defining a central processor unit and memories, and an additional layer of silicon that is sealed to the active face of the silicon substrate layer by a sealing layer, the additional layer of silicon covering at least part of said active face, the additional layer of silicon [and] comprising physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm .

Claim 2 (withdrawn).

Claim 3 (withdrawn).

Claim 4 (cancelled).

Claim 5 (previously amended): A chip according to claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are silicon dopants.

Claim 6 (previously amended): A chip according to claim 5, wherein the concentration of silicon dopants lies in the range 10^{17} to 10^{20} atoms per cm^3 , and is preferably about 10^{19} atoms per cm^3 .

Claim 7 (previously amended): A chip according to claim 5, wherein the silicon dopants are phosphorus or boron.

Claim 8 (cancelled)

Claim 9 (cancelled).

Claim 10 (previously amended): A chip according to claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by surface irregularities.

Claim 11 (cancelled).

Claim 12 (currently amended): A chip according to claim 10, wherein the surface irregularities are provided in the [bottom] face of the additional layer of silicon that is in contact with the sealing layer.

Claim 13 (currently amended): A chip according to claim 10, wherein the surface irregularities are provided in the [top] face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.

Claim 14 (currently amended): A chip according to claim 1, wherein the physical means for providing physical protection against the action of electromagnetic radiation are formed by at least one [layer] deposition of metal on the additional layer of silicon.

Claim 15 (currently amended): A chip according to claim 14, wherein the metal deposition [layer] has a thickness greater than 50 Å.

Claim 16 (currently amended): A chip according to claim 14, wherein the metal [deposition] is [places] on the [bottom] face of the additional [layer] of silicon that is in contact with the sealing layer.

Claim 17 (currently amended): A chip according to claim 14, wherein the metal [layer] deposition is [placed] on the [top] face of the additional layer of silicon that is opposite to the face that is in contact with the sealing layer.

Claim 18 (cancelled).

Claim 19 (currently amended): A chip according to claim 16, wherein the metal [layer] deposition has a thickness of about 100 Å

Claim 20 (new): A portable article provided with a chip that comprises a silicon substrate layer having an active face with circuits integrated therein defining a central processor unit and memories, the chip further comprising an additional layer of silicon that is sealed to the active face of the silicon substrate layer by a sealing layer, the additional layer of silicon covering at least part of said active face, the additional layer of silicon comprising physical means for providing physical protection against the action of electromagnetic radiation in the infrared range at a wavelength longer than 1 μm .